

L Number	Hits	S arch Text	DB	Tim stamp
-	2	(singl adj crystal).clm. and (amorphiz r am rphizing or amorphiz d or amorphizati n).clm. and laser.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:49
-	4526	yamamoto and fujitsu	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:47
-	1	(yamamoto and fujitsu) and (shallow and deep).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:46
-	2	yamamoto and tomonari and fujitsu	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:48
-	5353	parasitic adj resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:50
-	83	(parasitic adj resistance) and (single adj crystal).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:49
-	4	((parasitic adj resistance) and (single adj crystal).clm.) and laser.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:49
-	2	(parasitic adj resistance).ti,ab,clm. and (single adj crystal).ti,ab,clm. and laser.ti,ab,clm. and ion.ti,ab,clm. and (implant or implanting or implanted or implantation).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:52
-	1	((parasitic adj resistance).ti,ab,clm. and (single adj crystal).ti,ab,clm. and laser.ti,ab,clm. and ion.ti,ab,clm. and (implant or implanting or implanted or implantation).ti,ab,clm.) and (amorphous).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:52

-	0	((parasitic adj r sistence).ti,ab,clm. and (single adj rystal).ti,ab,clm. and laser.ti,ab, lm. and i n.ti,ab, lm. and (implant r implanting r implanted or implantati n).ti,ab,clm.) and (oblique).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:52
-	1	((parasitic adj resistance).ti,ab,clm. and (single adj crystal).ti,ab,clm. and laser.ti,ab,clm. and ion.ti,ab,clm. and (implant or implanting or implanted or implantation).ti,ab,clm.) and (oblique).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:52
-	2	(parasitic adj resistance) and (single adj crystal) and laser and ion and (implant or implanting or implanted or implantation) and oblique and (amorphous or amorphize or amorphized or amorphizing or amorphization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:53
-	38	(single adj crystal) and (oblique near5 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:56
-	0	((single adj crystal) and (oblique near5 laser)) and (parasitic near resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:56
-	633	(single adj crystal) and (oblique and laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:56
-	4	((single adj crystal) and (oblique and laser)) and (parasitic near resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:57
-	13	((single adj crystal) same laser same (oblique or slanted or slanting or diagonal)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 12:51
-	1	((single adj crystal) same laser same (oblique or slanted or slanting or diagonal) same (ion) same (implant or implanted or implanting or implantation)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 12:51
-	1	((singl adj crystal) same las r same ( blique or slant d r slanting r diagonal) sam (i n) same (implant r implanted or implanting r implantation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 12:51

-	439	((ingle adj crystal) and las r and ( blique r lanted r slanting or diag nal) and (i n) and (implant or implanted or implanting r implantati n))	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 12:52
-	8	((single adj crystal) and laser and (oblique or slanted or slanting or diagonal) and (ion) and (implant or implanted or implanting or implantation))) and ((amorphize or amorphizing or amorphized or amorphization or amorphous) same oblique)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 12:52
-	6	(parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:50
-	3	(parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (oblique or slant or slanted or diagonal) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:52
-	21	(parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	712	((ion near (implant or implanting or implanted or implantation)) near5 oblique)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	24	((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:54
-	2	((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized) same (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:54

-	2	((ion near (implant or implanting or implanted or implantation)) near5 oblique) and (single adjacent crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:55
-	31	((ion near (implant or implanting or implanted or implantation)) near5 oblique) and (amorphous or amorphize or amorphizing or amorphized)) and (single adjacent crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:55
-	11	((ion near (implant or implanting or implanted or implantation)) near5 oblique) and (amorphous or amorphize or amorphizing or amorphized)) and (single adjacent crystal) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:56
-	1	((amorphize or amorphized or amorphous or amorphizing) near5 oblique near5 (ion or atom)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:57
-	1	((amorphize or amorphized or amorphous or amorphizing) near10 oblique near10 (ion or atom)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:57
-	14	((amorphize or amorphized or amorphous or amorphizing) near10 oblique near10 (ion or atom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:58
-	625	(oblique near5 (ion or atom) near5 (implant or implantation or implanted or implantating))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:59
-	82	(oblique near5 (ion or atom) near5 (implant or implantation or implanted or implantating)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:59
-	0	(oblique near5 (ion or atom) near5 (implant or implantation or implanted or implantating)).clm. and laser.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:59
-	7	(oblique near5 (ion or atom) near5 (implant or implantation or implanted or implantating)).clm. and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:00

-	0	( oblique n ar5 (i n r at m) near5 (implant or implantati n r implantat d r implantating)),clm. and laser and (parasitic n ar resistanc e)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:00
-	14	(oblique near5 (ion or atom) near5 (implant or implantation or implanted or implantating)),clm. and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:00
-	9	(oblique near10 (ion or atom) near10 (implant or implantation or implanted or implantating)) and (single adj crystal) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:01
-	8	(oblique near10 (ion or atom) near10 (implant or implantation or implanted or implantating)) and (single adj crystal) and laser and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:01
-	2	(oblique near10 (ion or atom) near10 (implant or implantation or implanted or implantating)) and (single adj crystal) and laser and mask and (parasitic near resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:02
-	10159	((atom or ion) near (implant or implanting or implanted or implantation)),clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:03
-	0	((atom or ion) near (implant or implanting or implanted or implantation)),clm. and oblique.clm. and (parasitic near resistance) and (amorphous or amorphize or amorphizing or amorphized).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:04
-	12	((atom or ion) near (implant or implanting or implanted or implantation)),clm. and oblique.clm. and (amorphous or amorphize or amorphizing or amorphized).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:04
-	4	((atom or ion) near (implant or implanting or implanted or implantation)),clm. and oblique.clm. and (amorphous or amorphize or amorphizing or amorphized).clm. and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:06
-	2	gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphize or am rphizing or amorphiz d) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:08

-	1	gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:08
-	70	gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:09
-	9	gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask and (sidewall or (side near wall)) and junction and (impurity or impurities)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:11
-	2	gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask and (sidewall or (side near wall)) and junction and (impurity or impurities) and (shallow and deep)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:16
-	1	gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphizing or amorphized or amorphize) and (seeping or seep or seeped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:17
-	1	gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:17
-	1	gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:18

-	1	gate and source and drain and (single adjacent crystal) and (shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:18
-	1	(shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:18
-	1	(shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:18
-	1	(shallow near junction) and (deep near junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:19
-	55	(US-5569954-\$ or US-5824574-\$ or US-6001461-\$ or US-5709958-\$ or US-6534373-\$ or US-6391695-\$ or US-4597804-\$ or US-5955759-\$ or US-6458200-\$ or US-5698869-\$ or US-5291274-\$ or US-5229319-\$ or US-5908307-\$ or US-5736438-\$ or US-5514880-\$ or US-5693959-\$ or US-6610569-\$ or US-6524924-\$ or US-6455875-\$ or US-6315384-\$ or US-6267471-\$ or US-6180957-\$ or US-6133094-\$ or US-5962897-\$ or US-5930638-\$ or US-5793097-\$).did. or (US-6437367-\$ or US-6436815-\$ or US-5963278-\$ or US-5933205-\$ or US-5856228-\$ or US-5643806-\$ or US-5568288-\$ or US-5541124-\$ or US-5287205-\$ or US-6255146-\$ or US-6245622-\$ or US-6188085-\$ or US-6017781-\$ or US-5612230-\$ or US-5600154-\$ or US-5428237-\$ or US-5270227-\$ or US-5164806-\$ or US-6184088-\$).did. or (US-20020121654-\$ or US-20020073918-\$ or US-20020011627-\$).did. or (JP-2002280548-\$ or JP-2002329864-\$ or JP-63009152-\$ or JP-11087361-\$ or JP-09309713-\$ or JP-06267974-\$ or JP-05047794-\$).did.	USPAT; US-PGPUB; JPO	2003/09/15 15:19

-	1	((US-5569954-\$ r US-5824574-\$ or U -6001461-\$ r US-5709958-\$ r US-6534373-\$ r US-6391695-\$ or US-4597804-\$ r US-5955759-\$ or US-6458200-\$ r US-5698869-\$ r US-5291274-\$ or US-5229319-\$ or US-5908307-\$ or US-5736438-\$ or US-5514880-\$ or US-5693959-\$ or US-6610569-\$ or US-6524924-\$ or US-6455875-\$ or US-6315384-\$ or US-6267471-\$ or US-6180957-\$ or US-6133094-\$ or US-5962897-\$ or US-5930638-\$ or US-5793097-\$).did. or (US-6437367-\$ or US-6436815-\$ or US-5963278-\$ or US-5933205-\$ or US-5856228-\$ or US-5643806-\$ or US-5568288-\$ or US-5541124-\$ or US-5287205-\$ or US-6255146-\$ or US-6245622-\$ or US-6188085-\$ or US-6017781-\$ or US-5612230-\$ or US-5600154-\$ or US-5428237-\$ or US-5270227-\$ or US-5164806-\$ or US-6184088-\$).did. or (US-20020121654-\$ or US-20020073918-\$ or US-20020011627-\$).did. or (JP-2002280548-\$ or JP-2002329864-\$ or JP-63009152-\$ or JP-11087361-\$ or JP-09309713-\$ or JP-06267974-\$ or JP-05047794-\$).did.) and seeping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:19
-	271	seeping.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:19
-	5	seeping.clm. and junction.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:21
-	1	(source and drain and gate and (single adj crystal) and (atom or impurity or ion) and (shallow adj junction) and (deep adj junction) and capacitance).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:22
-	1	((single adj crystal) and (atom or impurity or ion) and (shallow adj junction) and (deep adj junction) and capacitance).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:22



-	22	((shallow adj junction) and (deep adj junction)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:23
-	5	((shallow adj junction) and (deep adj junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:24
-	2	((shallow adj junction) and (deep adj junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:25
-	3	((shallow near junction) and (deep near junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:26
-	0	((shallow near junction) and (deep near junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:25
-	1	((shallow near junction) and (deep near junction)) and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and laser and (single adj crystal) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:27
-	9	((shallow near junction) and (deep near junction)) and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and laser and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:28
-	4	(laser adj (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphize or amorphizing or amorphized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:30

-	4	(laser adj (irradiate r irradiatig r irradiated or irradiati n or anneal or annealing or anneal d)) and blique and ((atom r impurity ri n) near (implant r implanting or implant d or implantation)) and (amotphous or amorphize or amorphizing or amorphized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:30
-	101	(laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:30
-	4	(laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:31
-	4	(laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:32
-	4	(laser adj (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:32
-	5	(laser near (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single bear crystal) and ((deep or shallow) near juncti n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:33

-	4	(laser n ar (irradiat or irradiating or irradiat d r irradiation or ann al r annealing r annealed)) and oblique and ((atom r impurity ri n) near (implant r implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single near crystal) and ((deep or shallow) near junction)	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:35
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